Hui-Xiong Deng

List of Publications by Year in descending order

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33	1,720	19	33
papers	citations	h-index	g-index
35	35	35	2254
all docs	docs citations	times ranked	citing authors

#	Article	IF	CITATIONS
1	Machine learning in materials science. InformaÄnÃ-Materiály, 2019, 1, 338-358.	17.3	427
2	Large cation ethylammonium incorporated perovskite for efficient and spectra stable blue light-emitting diodes. Nature Communications, 2020, 11, 4165.	12.8	217
3	Thicknessâ€Dependent Carrier Transport Characteristics of a New 2D Elemental Semiconductor: Black Arsenic. Advanced Functional Materials, 2018, 28, 1802581.	14.9	125
4	Recent Advances of 2D Materials in Nonlinear Photonics and Fiber Lasers. Advanced Optical Materials, 2020, 8, 1901631.	7.3	122
5	Ultrafast photonics of two dimensional AuTe2Se4/3 in fiber lasers. Communications Physics, 2020, 3, .	5 . 3	93
6	Tunable electronic and optical properties of InSe/InTe van der Waals heterostructures toward optoelectronic applications. Journal of Materials Chemistry C, 2018, 6, 7201-7206.	5 . 5	87
7	Electronic structure and exciton shifts in Sb-doped MoS2 monolayer. Npj 2D Materials and Applications, 2019, 3, .	7.9	82
8	Unified theory of direct or indirect band-gap nature of conventional semiconductors. Physical Review B, 2018, 98, .	3 . 2	60
9	Reviewing and understanding the stability mechanism of halide perovskite solar cells. InformaÄnÃ- Materiály, 2020, 2, 1034-1056.	17. 3	55
10	Tuning transport performance in two-dimensional metal-organic framework semiconductors: Role of the metal $\langle i \rangle d \langle j \rangle$ band. Applied Physics Letters, 2018, 112, .	3.3	53
11	Thickness-Dependent Ultrafast Photonics of SnS ₂ Nanolayers for Optimizing Fiber Lasers. ACS Applied Nano Materials, 2019, 2, 2697-2705.	5.0	48
12	Quantum engineering of non-equilibrium efficient p-doping in ultra-wide band-gap nitrides. Light: Science and Applications, 2021, 10, 69.	16.6	42
13	Mixedâ€Valenceâ€Driven Quasiâ€1D Sn ^{ll} Sn ^{lV} S ₃ with Highly Polarizationâ€5ensitive UV–vis–NIR Photoresponse. Advanced Functional Materials, 2019, 29, 1904416.	14.9	39
14	Exceptional Optoelectronic Properties of Hydrogenated Bilayer Silicene. Physical Review X, 2014, 4, .	8.9	35
15	Symmetryâ€Reduction Enhanced Polarizationâ€Sensitive Photodetection in Core–Shell Sbl ₃ /Sb ₂ O ₃ van der Waals Heterostructure. Small, 2020, 16, e1907172.	10.0	32
16	Realistic dimension-independent approach for charged-defect calculations in semiconductors. Physical Review B, 2020, 101, .	3.2	30
17	Origin of the Distinct Diffusion Behaviors of Cu and Ag in Covalent and Ionic Semiconductors. Physical Review Letters, 2016, 117, 165901.	7.8	25
18	Quasiparticle Band Structure and Optical Properties of the Janus Monolayer and Bilayer SnSSe. Journal of Physical Chemistry C, 2020, 124, 23832-23838.	3.1	23

#	Article	IF	CITATIONS
19	Metal and ligand effects on the stability and electronic properties of crystalline two-dimensional metal-benzenehexathiolate coordination compounds. Journal of Physics Condensed Matter, 2018, 30, 465301.	1.8	20
20	Abnormal diffusion behaviors of Cu atoms in van der Waals layered material MoS $<$ sub $>$ 2 $<$ /sub $>$. Journal of Materials Chemistry C, 2019, 7, 6052-6058.	5.5	18
21	Donor–Acceptor Pair Quantum Emitters in Hexagonal Boron Nitride. Nano Letters, 2022, 22, 1331-1337.	9.1	17
22	A systematic study of the negative thermal expansion in zinc-blende and diamond-like semiconductors. New Journal of Physics, 2019, 21, 123015.	2.9	10
23	Deep insights into interface engineering by buffer layer for efficient perovskite solar cells: a first-principles study. Science China Materials, 2020, 63, 1588-1596.	6.3	10
24	Decoupling of the Electrical and Thermal Transports in Strongly Coupled Interlayer Materials. Journal of Physical Chemistry Letters, 2021, 12, 7832-7839.	4.6	8
25	Clarification of the relative magnitude of exciton binding energies in ZnO and SnO2. Applied Physics Letters, 2022, 120, .	3.3	8
26	Large lattice-relaxation-induced intrinsic shallow p-type characteristics in monolayer black phosphorus and black arsenic. Applied Physics Letters, $2021,118,$.	3.3	6
27	Orbital localization induced magnetization in nonmetal-doped phosphorene. Journal Physics D: Applied Physics, 2020, 53, 155001.	2.8	4
28	Manipulation of crystalline structure, magnetic performance, and topological feature in Mn3Ge films. APL Materials, 2021, 9, .	5.1	4
29	Band offset trends in IV–VI layered semiconductor heterojunctions. Journal of Physics Condensed Matter, 2022, 34, 195003.	1.8	3
30	Field-Effect Transistors: Thickness-Dependent Carrier Transport Characteristics of a New 2D Elemental Semiconductor: Black Arsenic (Adv. Funct. Mater. 43/2018). Advanced Functional Materials, 2018, 28, 1870312.	14.9	2
31	Electronic structures and band alignment transition in double-wall MoS ₂ /WS ₂ nanotubes for optoelectronic applications. Journal Physics D: Applied Physics, 2021, 54, 095105.	2.8	2
32	Polarizationâ€Sensitive Photodetectors: Symmetryâ€Reduction Enhanced Polarizationâ€Sensitive Photodetection in Core–Shell Sbl ₃ /Sb ₂ O ₃ van der Waals Heterostructure (Small 7/2020). Small, 2020, 16, 2070036.	10.0	1
33	Origin of the discrepancy between the fundamental and optical gaps and native defects in two dimensional ultra-wide bandgap semiconductor: Gallium thiophosphate. Applied Physics Letters, 2022, 120, 172108.	3.3	1